

# Diffraction from stepped surfaces

Surface Science

139, 121-154

DOI: [10.1016/0039-6028\(84\)90013-x](https://doi.org/10.1016/0039-6028(84)90013-x)

Citation Report

#	ARTICLE	IF	CITATIONS
1	X-ray scattering by gratings and dots. , 1999, , 221-246.		0
2	Transition From Single-Layer to Double-Layer Steps on GaAs(110) Prepared by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1984, 37, 431.	0.1	7
3	Analysis of Domain-Size Distributions in Epitaxial Growth Using Leed Angular Profiles. Materials Research Society Symposia Proceedings, 1984, 41, 179.	0.1	2
4	Distribution of domain sizes during overlayer growth. Surface Science Letters, 1985, 159, L467-L473.	0.1	0
5	More than one monolayer adsorption of oxygen on the W(112) surface. Physical Review B, 1985, 31, 1950-1953.	1.1	12
6	Integral representation of the diffracted intensity from one-dimensional stepped surfaces and epitaxial layers. Journal of Applied Physics, 1985, 58, 2184-2189.	1.1	27
7	Exact one-dimensional pair correlation functions of a monolayer/substrate system. Journal of Applied Physics, 1985, 57, 1121-1129.	1.1	47
8	Mass-action control of AlGaAs and GaAs growth in molecular beam epitaxy. Applied Physics Letters, 1985, 47, 726-728.	1.5	95
9	Two-dimensional atomic correlations of epitaxial layers. Journal of Applied Physics, 1985, 57, 4583-4588.	1.1	11
10	Diffraction from surfaces with interacting steps. Surface Science, 1985, 159, 169-183.	0.8	31
11	Diffraction from a surface with incommensurate domain walls. Surface Science, 1985, 154, 15-21.	0.8	46
12	Distribution of domain sizes during overlayer growth. Surface Science, 1985, 159, L467-L473.	0.8	1
13	Defects at semiconductor surfaces. Surface Science, 1985, 152-153, 963-976.	0.8	40
14	Diffraction from stepped surfaces. Surface Science, 1985, 161, 39-68.	0.8	242
15	Investigation of a randomly stepped Pt(111) surface using thermal energy atom scattering (TEAS). Surface Science, 1985, 162, 858-864.	0.8	51
16	Molecular beam epitaxy. Reports on Progress in Physics, 1985, 48, 1637-1697.	8.1	179
17	RHEED studies of heterojunction and quantum well formation during MBE growth " from multiple scattering to band offsets. Surface Science, 1986, 168, 423-438.	0.8	163
18	LEED studies of defects at surfaces and interfaces. Surface Science, 1986, 168, 744-750.	0.8	12

#	ARTICLE	IF	CITATIONS
19	Quantitative analysis of streaks in reflection high-energy electron diffraction: GaAs and AlAs deposited on GaAs(001). <i>Physical Review B</i> , 1986, 33, 8329-8335.	1.1	30
20	Surface effects and growth dynamics in MBE of III-V compounds. <i>Surface Science</i> , 1986, 178, 110-123.	0.8	23
21	Evidence for mono- and diatomic steps on a cleaved Os(0001) surface. <i>Surface Science</i> , 1986, 178, 452-461.	0.8	3
22	The determination of mbe growth mechanisms using dynamic reed techniques. <i>Surface Science</i> , 1986, 174, 1-9.	0.8	46
23	Quantitative evaluation of terrace width distributions from LEED measurements. <i>Surface Science</i> , 1986, 167, 534-548.	0.8	49
24	Dynamic effects in RHEED from MBE grown GaAs(001) surfaces. <i>Surface Science</i> , 1986, 169, 176-196.	0.8	102
25	Observation of Transient Behavior of GaAs MBE Growth by RHEED Oscillation. <i>Japanese Journal of Applied Physics</i> , 1986, 25, 1847-1850.	0.8	12
26	Be Doping Effect on Growth Kinetics of GaAs Grown by MBE. <i>Japanese Journal of Applied Physics</i> , 1986, 25, L81-L84.	0.8	29
27	Observation of surface roughening on Ni(115). <i>Journal of Chemical Physics</i> , 1986, 84, 1015-1028.	1.2	99
28	Influence of surface step density on reflection high-energy-electron diffraction specular intensity during epitaxial growth. <i>Physical Review B</i> , 1987, 36, 9312-9314.	1.1	35
29	Observation of Si(111) surface topography changes during Si molecular beam epitaxial growth using microprobe reflection high-energy electron diffraction. <i>Applied Physics Letters</i> , 1987, 50, 1141-1143.	1.5	125
30	Kosterlitz-Thouless roughening at the Ni(113) surface. <i>Surface Science</i> , 1987, 187, 265-288.	0.8	61
31	Rheed intensities from stepped surfaces. <i>Surface Science</i> , 1987, 187, 194-200.	0.8	44
32	Leed studies of Si molecular beam epitaxy onto Si(111). <i>Journal of Crystal Growth</i> , 1987, 81, 428-433.	0.7	46
33	Current understanding and applications of the RHEED intensity oscillation technique. <i>Journal of Crystal Growth</i> , 1987, 81, 1-8.	0.7	149
34	RHEED oscillation study by modulated electron beam during GaAs growth. <i>Journal of Crystal Growth</i> , 1987, 81, 9-12.	0.7	4
35	Reflection high energy electron diffraction measurement of surface diffusion during the growth of gallium arsenide by MBE. <i>Journal of Crystal Growth</i> , 1987, 81, 13-18.	0.7	114
36	Bethe's correction method for dynamical calculation of reflection high-energy electron diffraction intensities from general surfaces. <i>Acta Crystallographica Section A: Foundations and Advances</i> , 1988, 44, 1042-1044.	0.3	15

#	ARTICLE	IF	CITATIONS
37	Oscillations of specular beam intensity in reflection diffraction from the surface of a growing epitaxial film. A theoretical study. <i>Physica Status Solidi A</i> , 1988, 110, 61-76.	1.7	9
38	Determination of surface step distributions on Ge using RHEED. <i>Ultramicroscopy</i> , 1988, 26, 143-150.	0.8	4
39	Quantitative evaluation of the perfection of an epitaxial film grown by vapor deposition as determined by thermal energy atom scattering. <i>Journal of Crystal Growth</i> , 1988, 88, 442-454.	0.7	82
40	Growth kinetics and step density in reflection high-energy electron diffraction during molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1988, 63, 2272-2283.	1.1	157
41	Atomic and electronic structure of tetrahedrally coordinated compound semiconductor interfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1988, 6, 1957-1962.	0.9	22
42	Non-steady state effects in MBE: Oscillations of the step density at the crystal surface. <i>Surface Science</i> , 1988, 202, 109-124.	0.8	37
43	Direct determination of the size distribution of arbitrary surface configurations from diffraction measurements: General theory. <i>Surface Science</i> , 1988, 205, 591-616.	0.8	8
44	The use of peak intensity in diffraction measurements of growth kinetics on surfaces. <i>Surface Science</i> , 1988, 195, L159-L166.	0.8	25
45	Monte Carlo simulations of Si(001) growth and reconstruction during molecular beam epitaxy. <i>Surface Science</i> , 1988, 198, 133-150.	0.8	82
46	Defects in a W(112) surface. <i>Surface Science</i> , 1988, 194, L77-L86.	0.8	8
47	Surface X-Ray Scattering during Crystal Growth: Ge on Ge(111). <i>Physical Review Letters</i> , 1988, 61, 2241-2244.	2.9	155
48	Resistance oscillations and crossover in ultrathin gold films. <i>Physical Review B</i> , 1988, 37, 8622-8626.	1.1	84
49	Reversible faceting of the copper (110) surface: X-ray Fresnel reflectivity. <i>Physical Review B</i> , 1988, 38, 7378-7384.	1.1	55
50	Disordering of the (111) surface of germanium crystal near its bulk melting temperature. <i>Physical Review B</i> , 1988, 38, 13163-13177.	1.1	41
51	Surface structure and long-range order of the Ge(111)-c(2 $\times$ 8) reconstruction. <i>Physical Review B</i> , 1988, 38, 9715-9720.	1.1	85
52	Epitaxial growth and band bending of n- and p-type Ge on GaAs(001). <i>Physical Review B</i> , 1988, 38, 7484-7492.	1.1	36
53	Spot Profile Analysis for Studying Epitaxial Growth. <i>Studies in Surface Science and Catalysis</i> , 1988, 40, 237-239.	1.5	0
54	Defects at the Si(111)/SiO <sub>2</sub> interface investigated with low-energy electron diffraction. <i>Physical Review B</i> , 1989, 39, 6052-6059.	1.1	24

#	ARTICLE	IF	CITATIONS
55	Dynamical simulation of molecular-beam epitaxial growth of a model crystal. <i>Physical Review B</i> , 1989, 39, 1224-1228.	1.1	20
56	Diffraction determination of the size distribution of noncrystalline regions on a crystalline substrate. <i>Physical Review Letters</i> , 1989, 63, 402-405.	2.9	18
57	Use of cation-stabilized conditions to improve compatibility of CdTe and HgTe molecular beam epitaxy. <i>Applied Physics Letters</i> , 1989, 55, 1561-1563.	1.5	12
58	X-ray intensity oscillations occurring during growth of Ge on Ge(111)-a comparison with RHEED. <i>Journal of Physics Condensed Matter</i> , 1989, 1, SB213-SB214.	0.7	4
59	Low-energy ion beams, molecular beam epitaxy, and surface morphology. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 1989, 39, 72-80.	0.6	40
60	Current understanding of growth mechanisms in III-V MBE. <i>Journal of Crystal Growth</i> , 1989, 95, 11-16.	0.7	11
61	On the origin of RHEED intensity oscillations. <i>Journal of Crystal Growth</i> , 1989, 95, 23-27.	0.7	35
62	Influence of adsorption-site geometry and diffusion on thin-film growth: Pt/Pd(100). <i>Ultramicroscopy</i> , 1989, 31, 80-86.	0.8	8
63	Ordering kinetics at surfaces. <i>Ultramicroscopy</i> , 1989, 31, 87-98.	0.8	59
64	Continuous roughness characterization from atomic to micron distances: Angle-resolved electron and photon scattering. <i>Applied Surface Science</i> , 1989, 39, 457-472.	3.1	23
65	The initial stages of growth of silicon on Si(111) by slow positron annihilation low-energy electron diffraction. <i>Thin Solid Films</i> , 1989, 183, 213-220.	0.8	65
66	Rheed intensity calculations for Au(001) ultrathin films on an Ag(001) substrate and for an Au/Ag(001) superlattice. <i>Surface Science Letters</i> , 1989, 222, A547-A548.	0.1	2
67	Influence of surface morphology upon recovery kinetics during interrupted epitaxial growth. <i>Journal of Crystal Growth</i> , 1989, 95, 28-31.	0.7	21
68	Crystallographic analysis and observation of surface micro-areas using microprobe reflection high-energy electron diffraction. <i>Materials Science and Engineering Reports</i> , 1989, 4, 147-192.	5.8	59
69	Surface defects on Si(001). <i>Surface Science</i> , 1989, 207, 401-417.	0.8	21
70	Rheed intensity calculations for Au(001) ultrathin films on an Ag(001) substrate and for an Au/Ag(001) superlattice. <i>Surface Science</i> , 1989, 222, 247-258.	0.8	3
71	Observation of the surface roughening transition on Ni(117). <i>Surface Science</i> , 1989, 222, 477-490.	0.8	16
72	X-ray diffraction from rough, relaxed and reconstructed surfaces. <i>Surface Science</i> , 1989, 210, 301-321.	0.8	133

#	ARTICLE	IF	CITATIONS
73	Birth-death models of epitaxy. <i>Surface Science</i> , 1989, 216, 222-248.	0.8	256
74	Characteristic features in RHEED patterns of disordered surfaces: Theoretical considerations. <i>Surface Science</i> , 1989, 224, 591-612.	0.8	19
75	Random-deposition models for thin-film epitaxial growth. <i>Physical Review B</i> , 1989, 39, 5655-5664.	1.1	52
76	Epitaxy of FeAl films on GaAs(100) by molecular beam epitaxy. <i>Journal of Electronic Materials</i> , 1990, 19, 561-565.	1.0	5
77	Electron diffraction at stepped homogeneous and inhomogeneous surfaces. <i>Applied Physics A: Solids and Surfaces</i> , 1990, 50, 57-68.	1.4	111
78	Epitaxial growth of metals studied with thermal energy atom scattering. <i>Vacuum</i> , 1990, 41, 464-466.	1.6	4
79	SPA-LEED studies of defects in thin epitaxial NiSi <sub>2</sub> layers on Si(111). <i>Applied Surface Science</i> , 1990, 41-42, 230-235.	3.1	14
80	Modelling of epitaxial thin-film growth on fcc(100) substrates at low temperatures. <i>Vacuum</i> , 1990, 41, 479-481.	1.6	27
81	Direct evaluation of the multilevel distribution in epitaxial growth from electron diffraction. <i>Progress in Surface Science</i> , 1990, 35, 185-188.	3.8	0
82	Difference-equation approach in evaluating atomic correlation functions of stepped surfaces. <i>Chinese Physics Letters</i> , 1990, 7, 560-563.	1.3	1
83	Approach to thermal roughening of Ni(110): A study by high-resolution low-energy electron diffraction. <i>Physical Review Letters</i> , 1990, 64, 447-450.	2.9	100
84	Diffuse elastic scattering of atoms from surface steps. <i>Physical Review B</i> , 1990, 41, 8156-8163.	1.1	5
85	Low-temperature epitaxial growth of thin metal films. <i>Physical Review B</i> , 1990, 41, 5410-5413.	1.1	228
86	Defect cluster analysis for wafer-scale integration. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 1990, 3, 128-135.	1.4	20
87	Maximum entropy calculation of the island size distribution for a simple diffraction profile. <i>Journal of Applied Physics</i> , 1990, 68, 21-27.	1.1	29
88	Reflection high-energy electron diffraction oscillations during epitaxial growth of high-temperature superconducting oxides. <i>Physical Review Letters</i> , 1990, 65, 2684-2687.	2.9	332
89	Combined study of RHEED spot profiles and intensity oscillations during MBE growth of Ge on Ge(111). <i>Surface Science</i> , 1990, 230, L162-L168.	0.8	3
90	X-ray crystal truncation rod scattering: general intensity formula for no lateral displacements of surface atoms. <i>Surface Science</i> , 1990, 232, 417-425.	0.8	5

#	ARTICLE	IF	CITATIONS
91	On the RHEED specular beam and its intensity oscillation during MBE growth of GaAs. Surface Science, 1990, 231, 379-388.	0.8	58
92	Recovery kinetics during interrupted epitaxial growth. Surface Science, 1990, 225, 373-389.	0.8	98
93	Nonequilibrium lattice models of epitaxial growth. Surface Science, 1990, 232, 161-184.	0.8	14
94	Epitaxial growth of thin copper layers on Cu(111) studied by high-resolution low-energy-electron-diffraction. Surface Science, 1990, 231, 64-75.	0.8	36
95	Influence of surface disorder on RHEED patterns from GaAs(001) $\sqrt{2} \times \sqrt{2}$ surfaces. Surface Science, 1990, 240, 168-180.	0.8	21
96	Quantification of defects in epitaxial metal film growth: a helium diffraction investigation of the Cu/W(110) system. Surface Science, 1991, 255, 73-90.	0.8	20
97	Two-dimensional kinematic diffraction patterns from simulations of epitaxial growth. Surface Science, 1991, 241, 439-453.	0.8	10
98	Periodic changes in the structure of a surface growing under MBE conditions and RHEED oscillation. Surface Science, 1991, 242, 148-151.	0.8	8
99	Epitaxial submonolayer cobalt films on Cu(100) studied by X-ray diffraction. Surface Science, 1991, 250, L363-L367.	0.8	16
100	Determination of the distribution of steps on a surface from LEED spot profiles. Surface Science, 1991, 250, 207-219.	0.8	4
101	Diffraction profile analysis for epitaxial growth on fcc(100) substrates: diffusionless models. Surface Science, 1991, 256, 205-215.	0.8	11
102	Dynamical calculations for RHEED from MBE growing surfaces. I. Growth on a low-index surface. Proceedings of the Royal Society A, 1991, 432, 195-213.	1.0	15
103	Surface morphology of Ag(110) close to its roughening transition. Physical Review Letters, 1991, 67, 1890-1893.	2.9	54
104	High-Resolution Leed Study of Intermixing of Fe Films on Au(001) Surface. Materials Research Society Symposia Proceedings, 1991, 237, 429.	0.1	0
105	High-Resolution Low Energy Electron Diffraction Study of Surface Instabilities and Growth Dynamics. Materials Research Society Symposia Proceedings, 1991, 237, 49.	0.1	0
106	Scattering phases in low energy electron diffraction from spot profile analysis and from multiple scattering theory. Solid State Communications, 1991, 78, 671-675.	0.9	38
107	Epitaxial submonolayer cobalt films on Cu(100) studied by X-ray diffraction. Surface Science Letters, 1991, 250, L363-L367.	0.1	2
108	Control of MBE, MOMBE and CBE growth using RHEED. Applied Surface Science, 1991, 50, 28-33.	3.1	10

#	ARTICLE	IF	CITATIONS
109	Growth mechanism and superconducting properties of ultrathin $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ films. <i>Journal of Crystal Growth</i> , 1991, 115, 745-751.	0.7	6
110	Growth and characterization of iron aluminide films on compound semiconductors. <i>Journal of Electronic Materials</i> , 1991, 20, 319-324.	1.0	4
111	CCD-based reflection high-energy electron diffraction detection and analysis system. <i>Review of Scientific Instruments</i> , 1991, 62, 1263-1269.	0.6	30
112	High-resolution low-energy electron-diffraction analysis of the Pb(110) roughening transition. <i>Physical Review B</i> , 1991, 43, 4714-4727.	1.1	26
113	Thermal roughness of the homogeneous and inhomogeneous Cu(311) surface studied by high-resolution low-energy electron diffraction. <i>Physical Review B</i> , 1991, 44, 13031-13041.	1.1	44
114	Factors mediating smoothness in epitaxial thin-film growth. <i>Physical Review B</i> , 1991, 43, 3897-3905.	1.1	105
115	Observation of a Novel Double-Step Phase in Pb(110) Surface. <i>Europhysics Letters</i> , 1992, 19, 215-221.	0.7	17
116	Magnetic Moments in Rough Fe Surfaces. <i>Europhysics Letters</i> , 1992, 20, 65-70.	0.7	32
117	Evaluation of Atomic Correlation Functions for Stepped Inhomogeneous Surfaces. <i>Chinese Physics Letters</i> , 1992, 9, 530-533.	1.3	0
118	Measurements of dynamic scaling from epitaxial growth front: Fe film on Fe(001). <i>Physical Review Letters</i> , 1992, 69, 3770-3773.	2.9	150
119	As desorption from GaAs and AlAs surfaces studied by improved high-energy electron reflectivity measurements. <i>Journal of Applied Physics</i> , 1992, 71, 1753-1759.	1.1	15
120	X-ray crystal-truncation-rod analysis of untwinned $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ single crystals: The growth-termination plane. <i>Physical Review B</i> , 1992, 45, 5107-5110.	1.1	13
121	Time-invariant structure factor in an epitaxial growth front. <i>Physical Review Letters</i> , 1992, 68, 2612-2615.	2.9	40
122	Reflection high-energy electron-diffraction studies of the growth of $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ and $\text{DyBa}_2\text{Cu}_3\text{O}_{7-x}$ superconducting thin films. <i>Physical Review B</i> , 1992, 46, 8565-8572.	1.1	26
123	Reflection High Energy Electron Diffraction Studies of the Growth of $\text{DyBa}_2\text{Cu}_3\text{O}_{7-x}$ Films and Structures Grown on $\text{SrTiO}_3$ Substrates. <i>Materials Research Society Symposia Proceedings</i> , 1992, 275, 577.	0.1	0
124	A simple method to determine the step heights on ultrathin heteroepitaxial films. <i>Surface Science</i> , 1992, 273, L461-L466.	0.8	12
125	The initial stage of epitaxial growth of Ge on Ge(111) as studied by X-ray diffraction. <i>Surface Science</i> , 1992, 264, 281-291.	0.8	9
126	Growth, structure and morphology of ultrathin iron films on Cu(100). <i>Surface Science</i> , 1992, 264, 406-418.	0.8	119



#	ARTICLE	IF	CITATIONS
127	Helium diffraction analysis of the microfaceted Ir(110) surface. Surface Science, 1992, 274, 231-251.	0.8	20
128	Scaling analysis of surface roughness and Bragg oscillation decay in models for low-temperature epitaxial growth. Surface Science, 1992, 271, 321-330.	0.8	48
129	Adsorption induced reconstruction of the Cu(110) surface. Surface Science, 1992, 272, 94-101.	0.8	18
130	Initial growth morphology in molecular beam epitaxy of fcc iron on Cu(100). Surface Science, 1992, 272, 154-160.	0.8	37
131	Magnetic step anisotropies. Journal of Magnetism and Magnetic Materials, 1992, 113, 207-220.	1.0	70
132	Surface roughening, melting, and faceting. Progress in Surface Science, 1992, 39, 65-116.	3.8	81
133	Evaluation of the roughness of a crystal surface by X-ray scattering. I. Theoretical considerations. Acta Crystallographica Section A: Foundations and Advances, 1992, 48, 764-771.	0.3	30
134	Bloch wave treatment of symmetry and multiple beam cases in reflection high energy electron diffraction and reflection electron microscopy. Microscopy Research and Technique, 1992, 20, 360-370.	1.2	1
135	Kinematical calculations on reflection high-energy electron diffraction involving absorption. Journal of Crystal Growth, 1993, 133, 75-79.	0.7	4
136	Simulation of RHEED intensity oscillations during MBE growth. Journal of Crystal Growth, 1993, 127, 1025-1029.	0.7	3
137	Dynamical diffraction effect for RHEED intensity oscillations: phase shift of oscillations for glancing angles. Surface Science, 1993, 298, 261-272.	0.8	34
138	Surfactant induced layer-by-layer growth of Cu on Ru(0001) as revealed by oscillatory work function changes. Surface Science, 1993, 298, 173-186.	0.8	61
139	Kinetic faceting in homoepitaxy of Fe(110) on Fe(110). Surface Science, 1993, 294, 1-9.	0.8	68
140	Morphology of thin NaCl films grown epitaxially on Ge(100). Surface Science, 1993, 293, 57-66.	0.8	71
141	Promotion of epitaxial growth of Ge by Ag and Pb deposited on a clean Ge(111) surface. Surface Science, 1993, 281, 285-295.	0.8	21
142	Homoepitaxial growth on Pd(100). Surface Science, 1993, 289, 75-84.	0.8	24
143	Stacking faults in epitaxy investigated by SPALEED. Surface Science, 1993, 287-288, 964-968.	0.8	4
144	Chapter 1 Magnetism in ultrathin transition metal films. Handbook of Magnetic Materials, 1993, 7, 1-96.	0.6	65

#	ARTICLE	IF	CITATIONS
145	Island ordering on clean Pd(110). <i>Physical Review B</i> , 1993, 47, 13055-13058.	1.1	25
146	Order-disorder $(4\text{\AA}-2)-(2\text{\AA}-1)$ transition on Ge(001): An in situ x-ray scattering study. <i>Physical Review B</i> , 1993, 47, 10375-10382.	1.1	45
147	Diffraction from surface growth fronts. <i>Physical Review B</i> , 1993, 47, 3911-3922.	1.1	39
148	Homoepitaxial growth of iron and a real space view of reflection-high-energy-electron diffraction. <i>Physical Review Letters</i> , 1993, 70, 3615-3618.	2.9	289
149	Step-induced deconstruction and step-height evolution of the Au(110) surface. <i>Physical Review B</i> , 1993, 47, 12840-12851.	1.1	12
150	Temperature-dependent order of clean Pd(110). <i>Physical Review B</i> , 1993, 48, 14577-14583.	1.1	13
151	Initial evolution of Kashchiv models of thin-film growth. <i>Journal of Physics A</i> , 1993, 26, 2743-2754.	1.6	5
152	Observation of atomic place exchange in submonolayer heteroepitaxial Fe/Au(001) films. <i>Physical Review Letters</i> , 1993, 71, 3834-3837.	2.9	48
153	Spot-profile-analyzing LEED study of the epitaxial growth of Fe, Co, and Cu on Cu(100). <i>Physical Review B</i> , 1993, 48, 14509-14519.	1.1	50
154	Diffuse reflection high-energy electron diffraction. <i>Physical Review B</i> , 1993, 48, 8345-8355.	1.1	25
155	Phase Shift and Frequency Doubling on Intensity Oscillations of Reflection High-Energy Electron Diffraction: One-Beam Dynamical Calculations for Ge on Ge(111) Surface. <i>Japanese Journal of Applied Physics</i> , 1994, 33, L377-L379.	0.8	19
156	Contribution of reflection high-energy electron diffraction to nanometre tailoring of surfaces and interfaces by molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 1994, 9, 123-136.	1.0	42
157	Strain relief by microroughness in surfactant-mediated growth of Ge on Si(001). <i>Physical Review B</i> , 1994, 50, 11640-11652.	1.1	46
158	Instability in Low-Temperature Molecular-Beam Epitaxy Growth of Si/Si(111). <i>Physical Review Letters</i> , 1994, 73, 2348-2351.	2.9	73
159	Effect of atomic oxygen on the initial growth mode in thin epitaxial cuprate films. <i>Physical Review B</i> , 1994, 49, 3483-3491.	1.1	64
160	Helium scattering from disordered surfaces. <i>Computer Physics Communications</i> , 1994, 80, 32-52.	3.0	2
161	Evidence for surface melting during the growth of high $T_c$ thin films. <i>Physica C: Superconductivity and Its Applications</i> , 1994, 235-240, 697-698.	0.6	7
162	The roughening of metal surfaces. <i>Surface Science Reports</i> , 1994, 20, 195-249.	3.8	157

#	ARTICLE	IF	CITATIONS
163	Origin of phase shift phenomena in RHEED intensity oscillation curves. Ultramicroscopy, 1994, 55, 321-328.	0.8	11
164	Epitaxial Growth of Metallic Structures. , 1994, , 177-303.		2
165	Evolution of the missing row deconstruction on Rh (110). Surface Science, 1994, 318, L1193-L1200.	0.8	7
166	Nucleation and growth kinetics of GaAs during molecular beam epitaxy. Surface Science, 1994, 314, 79-88.	0.8	15
167	Disorder-order evolution of InSb(110) studied by He scattering. Surface Science, 1994, 307-309, 519-525.	0.8	9
168	Atomistic calculations on low-temperature layer-by-layer growth. Surface Science, 1994, 307-309, 526-530.	0.8	3
169	The equilibrium crystal shape and the roughening transition on metal surfaces. Surface Science, 1994, 299-300, 391-404.	0.8	33
170	Low-temperature, flux-independent epitaxy in Ag/Si(111). Surface Science, 1994, 302, 37-48.	0.8	13
171	Monte Carlo simulation and dynamic scaling of surfaces in MBE growth. Physical Review B, 1994, 49, 10597-10606.	1.1	29
172	Statistical treatment of dynamical electron diffraction from growing surfaces. Physical Review B, 1994, 50, 14525-14538.	1.1	27
173	Roughness Analysis of Si <sub>1-x</sub> Ge <sub>x</sub> Films. Materials Research Society Symposia Proceedings, 1994, 355, 301.	0.1	1
174	New Developments of Electron Diffraction Theory. Advances in Imaging and Electron Physics, 1994, 90, 205-351.	0.1	6
175	Epitaxy and thermal behaviour of metastable metal films. Progress in Surface Science, 1995, 48, 275-286.	3.8	2
176	Recent progress in low-energy electron diffraction: theory and application to semiconductor surfaces. Materials Science and Engineering Reports, 1995, 14, 255-317.	14.8	3
177	Time-resolved reflection high energy electron diffraction study of dynamical surface processes during molecular beam epitaxy of GaAs and AlAs. Journal of Crystal Growth, 1995, 146, 344-348.	0.7	3
178	Characterization of beryllium-doped molecular beam epitaxial grown GaAs by photoluminescence. Journal of Crystal Growth, 1995, 148, 35-40.	0.7	35
179	Reconstruction and disordering on (110) fcc metal surfaces. Progress in Surface Science, 1995, 48, 221-232.	3.8	8
180	Surface X-ray crystallography of growing crystals and interfaces. Nuclear Instruments & Methods in Physics Research B, 1995, 97, 358-363.	0.6	4

#	ARTICLE	IF	CITATIONS
181	Quantitative study of the decay of intensity oscillations in transient layer-by-layer growth. Physical Review B, 1995, 51, 17932-17945.	1.1	18
182	High Resolution Low Energy Electron Diffraction Study of Flattening on the TiO <sub>2</sub> (110) Surface. Physical Review Letters, 1995, 74, 4487-4490.	2.9	27
183	Terrace distribution during sputtering and recovery of InSb(110) studied by He-atom scattering. Physical Review B, 1995, 52, 14941-14946.	1.1	3
184	Vacancy island nucleation and inverse growth of InSb(110). Physical Review B, 1995, 51, 17957-17964.	1.1	8
185	Formation of facets and pyramidlike structures in molecular-beam-epitaxy growth of Si on a singular Si(111) surface. Physical Review B, 1995, 51, 14293-14299.	1.1	3
186	Molecular modelling of the chemical interaction of atoms and molecules with a surface. Russian Chemical Reviews, 1995, 64, 599-625.	2.5	2
187	Reflection High Energy Electron Diffraction Studies of the Dynamics of Molecular Beam Epitaxy. , 1995, , 669-744.		1
188	Scaling of island size distribution and island coalescence in monolayer epitaxial growth of 1 Å– 1 films. Surface Science, 1995, 324, 357-364.	0.8	23
189	Inverse growth kinetics on InSb(110). Surface Science, 1995, 323, L305-L310.	0.8	8
190	Dynamical electron scattering from growing surfaces. Surface Science, 1995, 324, L355-L361.	0.8	6
191	The temperature dependent growth mode of nickel on the basal plane of graphite. Surface Science, 1995, 327, 321-329.	0.8	36
192	The effect of Sb on the nucleation and growth of Ag on Ag(100). Surface Science, 1995, 330, 101-112.	0.8	33
193	A SPALEED structural study of cesium adsorption on stepped copper surfaces Cu(211) and Cu(511). Surface Science, 1995, 340, 265-280.	0.8	19
194	Evidence for a deconstructed "even" flat phase on the Pd(110) + K 1 Å– 2 surface. Surface Science, 1995, 322, 256-270.	0.8	5
195	Diffraction Methods. Handbook of Surface Science, 1996, 1, 271-360.	0.3	2
196	Multilayer Scaling and Universal Behavior of Molecular Beam Epitaxy Grown Surfaces. Langmuir, 1996, 12, 29-35.	1.6	4
197	Wave fields in Si(111) layers under RHEED conditions. Surface Science, 1996, 348, 344-358.	0.8	8
198	Dynamical Monte Carlo studies of molecular beam epitaxial growth models: interfacial scaling and morphology. Surface Science, 1996, 364, 151-163.	0.8	33

#	ARTICLE	IF	CITATIONS
199	Preparation-dependent surface composition and structure of NiAl(001): SPA-LEED and NICISS study. Surface Science, 1996, 366, 107-120.	0.8	48
200	RHEED intensity oscillations observed during growth of Ge on Si(111) substrates. Surface Science, 1996, 369, 91-98.	0.8	14
202	Interface Roughness in Strained Si/SiGe Multilayers. Materials Research Society Symposia Proceedings, 1996, 448, 153.	0.1	1
203	Monte Carlo simulation of simple models for thin film growth by MBE. Thin Solid Films, 1996, 272, 184-194.	0.8	22
204	Diffraction spot profile analysis for heteroepitaxial surfaces applied to the initial growth stages of CaF <sub>2</sub> adlayers on Si(111). Applied Surface Science, 1996, 104-105, 392-401.	3.1	10
205	Perturbation theory of diffuse RHEED applied to rough surfaces: Comparison with supercell calculations. Physical Review B, 1996, 54, 2121-2137.	1.1	11
206	Ordering of a prototypical conjugated molecular system during monolayer growth on the (1 $\bar{A}$ -2)-Au(110) surface. Physical Review B, 1996, 53, 1095-1098.	1.1	26
207	Two-layer behaviour during low-energy ion ablation of CdTe(001) studied by in situ X-ray diffraction and by Monte Carlo simulation. Europhysics Letters, 1996, 36, 271-276.	0.7	11
208	Role of the Step Density in Reflection High-Energy Electron Diffraction: Questioning the Step Density Model. Physical Review Letters, 1997, 78, 2381-2384.	2.9	54
209	Interference shift due to local variation of the attractive well in atom-surface scattering from small islands. Physical Review B, 1997, 56, 6490-6493.	1.1	12
210	Inelastic Scattering in Reflection High-Energy Electron Diffraction from Si(111). Physical Review Letters, 1997, 79, 4393-4396.	2.9	3
211	Step Height Oscillations during Layer-by-Layer Growth of Pb on Ge(001). Physical Review Letters, 1997, 79, 1527-1530.	2.9	58
212	Grazing-incidence x-ray scattering from stepped interfaces in AlAs/GaAs superlattices. Physical Review B, 1997, 56, 10469-10482.	1.1	33
213	Initial growth morphology in a heteroepitaxial system at low temperature: Fe on Ag(100). Physical Review B, 1997, 56, 4233-4242.	1.1	27
214	Metal Deposits on Thin Well Ordered Oxide Films: Morphology, Adsorption and Reactivity. , 1997, , 61-104.		21
215	Chapter 5 Heteroepitaxial metal growth: the effects of strain. Chemical Physics of Solid Surfaces, 1997, , 149-206.	0.3	18
216	A SPALEED structural study of lead adsorption on stepped copper surfaces Cu(211) and Cu(511). Surface Science, 1997, 371, 169-182.	0.8	8
217	A comparative STM and SPA-LEED study on the evolution of strain induced stripe pattern on Cu/Ni(100). Surface Science, 1997, 376, 113-122.	0.8	13

#	ARTICLE	IF	CITATIONS
218	Diffraction by a surface with random terrace distribution: an analytical calculation. Surface Science, 1997, 384, 15-35.	0.8	15
219	RHEED investigations of MBE-growth kinetics of Si on Si(111) and SiC on SiC(100). Surface Science, 1997, 383, 370-377.	0.8	12
220	Vertical layer distribution and atomic step height of ultrathin Co films on Cu(001) determined by lattice G-factor analysis. Surface Science, 1997, 388, 103-109.	0.8	3
221	Reconstruction, morphology, and stoichiometry of CdTe(001) and Cd <sub>0.96</sub> Zn <sub>0.04</sub> Te(001) surfaces. Surface Science, 1997, 388, 186-200.	0.8	14
222	RHEED intensity oscillations observed during the growth of YSi <sub>2</sub> x on Si(111) substrates. Surface Science, 1997, 391, 226-236.	0.8	5
223	Model of the adsorption/desorption kinetics on a growing III-V compound surface. Surface Science, 1997, 393, 108-125.	0.8	25
224	Ag-mediated step-bunching instability on vicinal Si(100). Surface Science, 1997, 394, 60-70.	0.8	25
225	Monte-Carlo simulation of Ge on Si(111) MBE growth: analysis of percolative structure. Thin Solid Films, 1997, 306, 220-223.	0.8	2
226	Influence of multilevel crystallization on the intensity oscillations of diffracted highenergy electrons during growth of aluminum arsenide by molecular beam epitaxy. Technical Physics Letters, 1997, 23, 307-308.	0.2	0
227	X-ray reflectivity reciprocal space mapping of strained SiGe/Si superlattices. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1997, 19, 419-428.	0.4	9
228	Incoherent scattering of electrons by a crystal surface. Micron, 1997, 28, 139-158.	1.1	7
229	Distributed growth model used for the interpretation of RHEED intensity oscillations observed during the growth of Pb on Si(111) substrates. Thin Solid Films, 1997, 306, 228-230.	0.8	1
230	Adsorption of Gases on Complex Solid Surfaces. Angewandte Chemie International Edition in English, 1997, 36, 452-475.	4.4	264
231	Adsorption von Gasen an komplexen Festkörp̄rperoberfl̄chen. Angewandte Chemie, 1997, 109, 444-468.	1.6	82
232	In situ detection of misfit dislocations by light scattering. Journal of Crystal Growth, 1997, 174, 550-557.	0.7	4
233	TEM-investigation on the critical thickness anisotropy of MBE-grown ZnSe/GaAs and Zn <sub>1-x</sub> MgxSe/GaAs. Journal of Crystal Growth, 1998, 184-185, 85-89.	0.7	4
234	New information on the sublimating CdTe(001) surface from high resolution LEED. Applied Surface Science, 1998, 123-124, 71-75.	3.1	6
235	Pulsed laser deposition and characterization of high-Tc YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> superconducting thin films. Materials Science and Engineering Reports, 1998, 22, 113-185.	14.8	76

#	ARTICLE	IF	CITATIONS
236	Surface morphology of laser superheated Pb(111). Surface Science, 1998, 405, 271-279.	0.8	6
237	Diffraction by a surface with terraces distribution: the Phase Matrix Method. Surface Science, 1998, 409, 403-412.	0.8	16
238	Characterization of epitaxial rubidium films with helium-atom scattering. Surface Science, 1998, 412-413, 12-23.	0.8	8
239	Behaviors of Auger Intensities Emitted from a Si(111) $\sqrt{3}\times\sqrt{3}$ -Al Surface During Incident Beam Rocking of Reflection High-Energy Electron Diffraction. Japanese Journal of Applied Physics, 1998, 37, L164-L166.	0.8	16
240	Beyond Intensity Oscillations. Surface Review and Letters, 1998, 05, 899-912.	0.5	6
241	Diffraction characterization of rough films formed under stable and unstable growth conditions. Physical Review B, 1998, 57, 15541-15552.	1.1	26
242	RHEED intensity oscillations observed during the growth of CaF <sub>2</sub> on Si(111). Physical Review B, 1998, 57, 12443-12447.	1.1	11
243	Atomic-scale structure of SiO <sub>2</sub> /Si interface formed by furnace oxidation. Physical Review B, 1998, 58, 13670-13676.	1.1	44
244	Effects of defect structures at surfaces and thin films on grazing scattering of fast ions. Physical Review B, 1998, 57, 15496-15506.	1.1	61
245	Temperature dependence of step density on vicinal Pb(111). Physical Review B, 1998, 57, 15561-15566.	1.1	0
246	Termination, surface structure and morphology of the molecular beam epitaxially grown HgTe(001) surface. Applied Physics Letters, 1998, 73, 3205-3207.	1.5	14
247	Fundamental relation between wave fields, rocking curves, and anomalous absorption for the reflection high-energy electron diffraction of Si(111) crystals. Physical Review B, 1998, 57, 4736-4746.	1.1	5
248	Surface morphology of laser-superheated Pb(111) and Pb(100). Physical Review B, 1998, 57, 9262-9269.	1.1	11
249	Prefactor and Step Edge Barrier Determination for Interlayer Diffusion in Homoepitaxial Systems: Ag/Ag(111). Surface Review and Letters, 1998, 05, 833-840.	0.5	15
250	Direct Observations of the Strain-Limited Island Growth of Sn-Doped GaAs(100). Surface Review and Letters, 1998, 05, 783-795.	0.5	3
251	Atomic beam diffraction from solid surfaces. Reports on Progress in Physics, 1998, 61, 1575-1664.	8.1	431
252	Diffraction analysis of a disordered surface, modelled on a probability distribution of reconstructed blocks: $n=6.45$ . Journal of Physics Condensed Matter, 1999, 11, 1935-1951.	0.7	5
253	How to use oxygen and atomic hydrogen to prepare atomically flat fcc Co(110) films. Europhysics Letters, 1999, 46, 589-594.	0.7	14

#	ARTICLE	IF	CITATIONS
254	INTERPRETATION OF REFLECTION HIGH ENERGY ELECTRON DIFFRACTION FROM DISORDERED SURFACES: DYNAMICAL THEORY AND ITS APPLICATION TO THE EXPERIMENT. <i>Surface Review and Letters</i> , 1999, 06, 461-495.	0.5	2
255	Reflection high-energy electron diffraction intensity oscillation during layer-by-layer oxidation of Si(001) surfaces. <i>Applied Physics Letters</i> , 1999, 74, 3284-3286.	1.5	17
256	Convergent N <sup>2</sup> -scaling iterative method of photoelectron diffraction and low-energy electron diffraction for ordered or disordered systems. <i>Physical Review B</i> , 1999, 59, 1657-1660.	1.1	12
257	Local layer-by-layer growth of Ni on hydrogen-terminated diamond C(111): A combined helium-atom scattering and XPS study. <i>Physical Review B</i> , 1999, 60, 11707-11715.	1.1	20
258	RHEED FROM EPITAXIALLY GROWN THIN FILMS. <i>Surface Review and Letters</i> , 1999, 06, 497-516.	0.5	11
259	Metal deposits on well-ordered oxide films. <i>Progress in Surface Science</i> , 1999, 61, 127-198.	3.8	931
260	Influence of miscut on crystal truncation rod scattering. <i>Journal of Applied Crystallography</i> , 1999, 32, 143-153.	1.9	21
261	Smoothing kinetics of CdTe(001)-surfaces: indication for a step/terrace exchange barrier. <i>Journal of Crystal Growth</i> , 1999, 201-202, 93-96.	0.7	2
262	Submonolayer homoepitaxy on Fe(100) studied by grazing ion surface scattering: experiments and computer simulations. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 1999, 157, 291-296.	0.6	1
263	Effect of Surface Plasmons on Energy Filtered RHEED Rocking Curves from a Si(111)-7Å-7 Surface. <i>Physica Status Solidi A</i> , 1999, 176, 925-936.	1.7	1
264	Origin of intensity oscillations in grazing ion scattering during epitaxial growth: a computational approach. <i>Surface Science</i> , 1999, 421, 263-272.	0.8	14
265	The Cu <sub>3</sub> Au(001) surface: a He diffraction study. <i>Surface Science</i> , 1999, 433-435, 307-311.	0.8	17
266	Temperature effects on morphology and composition of ultrathin heteroepitaxial films: Fe on Ag(100). <i>Surface Science</i> , 1999, 429, 34-45.	0.8	10
267	Mechanism of Layer-by-Layer Oxidation of Si(001) Surfaces by Two-Dimensional Oxide-Island Nucleation at SiO <sub>2</sub> /Si Interfaces. <i>Japanese Journal of Applied Physics</i> , 2000, 39, 2015-2020.	0.8	29
268	Initial stages of growth of Fe on Cu <sub>3</sub> Au(001) at low temperature: Formation of two-layer-thick islands. <i>Physical Review B</i> , 2000, 62, 13121-13128.	1.1	12
269	Temperature dependence of RHEED oscillation in homoepitaxial growth of SrTiO <sub>3</sub> (100) films on stepped substrates. <i>Surface Science</i> , 2000, 449, L235-L242.	0.8	7
270	Morphology of fcc Co(110) films on Cu(110). <i>Surface Science</i> , 2000, 454-456, 741-745.	0.8	9
271	A UNION OF THE REAL-SPACE AND RECIPROCAL-SPACE VIEW OF THE GaAs(001) SURFACE. <i>International Journal of Modern Physics B</i> , 2001, 15, 2301-2333.	1.0	8



#	ARTICLE	IF	CITATIONS
272	Growth of Co on Cu(111): Temperature dependence and interlayer spacings. Physical Review B, 2001, 64, .	1.1	5
273	Formation and commensurate analysis of $\sqrt{2} \times \sqrt{2}$ incommensurate superstructures of Pb on Si(111). Surface Science, 2001, 471, 11-20.	0.8	22
274	Strain measurement in ultra-thin films using RHEED and X-ray techniques. , 2001, , 173-200.		0
275	THERMAL OXIDATION OF SILICON AND Si-SiO <sub>2</sub> INTERFACE MORPHOLOGY, STRUCTURE AND LOCALIZED STATES. , 2001, , 115-216.		9
276	Two-Dimensional Fractal Surfaces. Experimental Methods in the Physical Sciences, 2001, , 255-272.	0.1	0
277	Reconstruction of the CoGa(100) surface studied by thermal-energy helium-atom scattering, LEED, and AES. Physical Review B, 2001, 63, .	1.1	9
278	Enabling electron diffraction as a tool for determining substrate temperature and surface morphology. Applied Physics Letters, 2001, 79, 3065-3067.	1.5	24
279	Atomic hydrogen cleaning of InP(100): Electron yield and surface morphology of negative electron affinity activated surfaces. Journal of Applied Physics, 2002, 91, 1256-1264.	1.1	9
280	Atomic geometry and the probability distribution of self-assembled Cs nanowires at the InAs(110) surface. Physical Review B, 2002, 66, .	1.1	9
281	Morphological and electronic properties of ultrathin crystalline silica epilayers on a Mo(112) substrate. Physical Review B, 2002, 66, .	1.1	85
282	Understanding crystal growth in vacuum and beyond. Surface Science, 2002, 500, 458-474.	0.8	39
283	Time-resolved electron diffraction study of the Ge(111)-(2 $\times$ 1) $\rightarrow$ (1 $\times$ 1) phase transition. Surface Science, 2002, 497, 373-384.	0.8	20
284	Temperature dependent reflection electron diffraction study of In(111) and observation of laser-induced transient surface superheating. Surface Science, 2002, 498, 275-284.	0.8	25
285	Layer-by-layer growth of GaAs(111) studied by in situ synchrotron X-ray diffraction. Surface Science, 2003, 525, 126-136.	0.8	26
286	Quantum size effects in the low temperature layer-by-layer growth of Pb on Ge(001). Progress in Surface Science, 2003, 72, 135-159.	3.8	31
287	Lineshape analysis of RHEED pattern: scaling behavior and linewidth oscillations. Thin Solid Films, 2003, 428, 72-75.	0.8	6
288	Role of aperiodic surface defects on the intensity of electron diffraction spots. Applied Physics Letters, 2003, 82, 2586-2588.	1.5	0
289	Combined molecular beam epitaxy and diffractometer system for in situ x-ray studies of crystal growth. Review of Scientific Instruments, 2003, 74, 1267-1273.	0.6	76

#	ARTICLE	IF	CITATIONS
290	Surface Study by Energy-Filtered RHEED-AES.. Hyomen Kagaku, 2003, 24, 145-152.	0.0	2
292	Non-Ostwald coarsening of the GaAs(001) surface. Physical Review B, 2004, 69, .	1.1	11
293	Characterizing single crystal surfaces using high resolution electron diffraction. Analytical and Bioanalytical Chemistry, 2004, 379, 588-93.	1.9	1
294	Two stages of post-growth recovery in molecular beam epitaxy: a surface X-ray diffraction study. Surface Science, 2004, 560, 88-102.	0.8	8
295	Comment on: $\alpha(2\times 1)-(1\times 1)$ phase transition on Ge(001): quasi-chemical approximation and Monte Carlo simulations [Surface Science 563 (2004) 99-109]. Surface Science, 2004, 573, 327-331.	0.8	2
296	Roughness and stability of silicon on insulator surfaces. Applied Physics Letters, 2004, 84, 350-352.	1.5	7
297	Design of a film surface roughness-minimizing molecular beam epitaxy process by reduced-order modeling of epitaxial growth. Journal of Applied Physics, 2004, 95, 483-489.	1.1	19
298	Recovery kinetics of the GaAs(001) surface in molecular beam epitaxy studied by in situ X-ray diffraction. Physica B: Condensed Matter, 2005, 357, 165-169.	1.3	3
299	Si nanostripe formation on vicinal Ge(100) surfaces. Surface Science, 2005, 574, 205-213.	0.8	2
300	Remark to the Intensity Measurement of RHEED. Instruments and Experimental Techniques, 2005, 48, 679-682.	0.1	0
301	Persistent Step-Flow Growth of Strained Films on Vicinal Substrates. Physical Review Letters, 2005, 95, 095501.	2.9	119
302	Growth Information Carried by Reflection High-Energy Electron Diffraction. , 2005, , 221-237.		3
304	Initial stages of MnAs/GaAs(001) epitaxy studied by RHEED azimuthal scans. Surface Science, 2006, 600, 3950-3955.	0.8	8
305	X-ray scattering from real surfaces: Discrete and continuous components of roughness. Physical Review B, 2006, 74, .	1.1	24
306	Real time observation of ultrathin epitaxial oxide growth during alloy oxidation. New Journal of Physics, 2007, 9, 331-331.	1.2	9
307	On the phase shift of reflection high energy electron diffraction intensity oscillations during Ge(001) homoepitaxy by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 221-224.	0.9	15
308	Dynamics of Step Bunching in Heteroepitaxial Growth on Vicinal Substrates. Physical Review Letters, 2007, 99, 055503.	2.9	31
309	Modeling RHEED intensity oscillations in multilayer epitaxy: Determination of the Ehrlich-Schwoebel barrier in Ge(001) homoepitaxy. Physical Review B, 2007, 76, .	1.1	18

#	ARTICLE	IF	CITATIONS
310	Nucleation, coarsening and kinetic scaling of two-dimensional islands on GaSb(001). <i>Surface Science</i> , 2007, 601, 814-821.	0.8	9
311	X-ray scattering from stepped and kinked surfaces: An approach with the paracrystal model. <i>Surface Science</i> , 2007, 601, 1915-1929.	0.8	10
312	The structure of the $\hat{1}\pm$ -quartz (0001) surface investigated using helium atom scattering and atomic force microscopy. <i>Surface Science</i> , 2007, 601, 4407-4411.	0.8	42
313	Homoepitaxial growth of Bi(111). <i>Physical Review B</i> , 2008, 78, .	1.1	19
314	Kink ordering and organized growth of Co clusters on a stepped Au(111) surface: A combined grazing-incidence x-ray scattering and STM study. <i>Physical Review B</i> , 2008, 77, .	1.1	17
315	Growth of praseodymium oxide on Si(111) under oxygen-deficient conditions. <i>Physical Review B</i> , 2009, 80, .	1.1	14
316	Probing surface and interface morphology with Grazing Incidence Small Angle X-Ray Scattering. <i>Surface Science Reports</i> , 2009, 64, 255-380.	3.8	686
317	Energy Dependence of Total Cross Section for Scattering of Helium Atoms from Isolated Atomic Steps. <i>Journal of the Bangladesh Academy of Sciences</i> , 2010, 34, 23-31.	0.1	0
318	Lost in reciprocal space? Determination of the scattering condition in spot profile analysis low-energy electron diffraction. <i>Review of Scientific Instruments</i> , 2011, 82, 035111.	0.6	9
319	X-ray diffraction from nonperiodic layered structures with correlations: analytical calculation and experiment on mixed Aurivillius films. <i>Acta Crystallographica Section A: Foundations and Advances</i> , 2012, 68, 148-155.	0.3	15
320	Plausible quantum-mechanical interpretations of RHEED oscillation. <i>Vacuum</i> , 2012, 86, 620-622.	1.6	1
322	X-ray Diffraction Study of Crystal Growth Dynamics during Molecular-Beam Epitaxy of III-V Semiconductors. <i>Journal of the Physical Society of Japan</i> , 2013, 82, 021011.	0.7	11
323	In-situ Materials Characterization. <i>Springer Series in Materials Science</i> , 2014, , .	0.4	17
324	Origin of RHEED intensity oscillation during homoepitaxial growth on Si(001). <i>Surface Science</i> , 2014, 630, 125-135.	0.8	2
325	The Structural and Optical Properties of Be-Doped GaAs Grown by MBE. <i>Advanced Materials Research</i> , 0, 1118, 111-117.	0.3	0
326	Complex oxide growth using simultaneous <i>in situ</i> reflection high-energy electron diffraction and x-ray reflectivity: When is one layer complete?. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	21
327	In Situ Characterization of Epitaxy. , 2015, , 1169-1209.		2
328	Au-chains grown on Ge(100): A detailed SPA-LEED study. <i>Surface Science</i> , 2015, 632, 64-70.	0.8	13

#	ARTICLE	IF	CITATIONS
329	Two-dimensional interaction of spin chains in the Si(553)-Au nanowire system. Physical Review B, 2016, 94, .	1.1	32
330	Crystal Surface Studies by Reflection High-Energy Electron Diffraction. Journal of the Vacuum Society of Japan, 2016, 59, 19-25.	0.3	1
331	The role of surface and interface structure in crystal growth. Progress in Crystal Growth and Characterization of Materials, 2016, 62, 203-211.	1.8	5
332	Synthesis of CdS thin films at room temperature by RF-magnetron sputtering and study of its structural, electrical, optical and morphology properties. Thin Solid Films, 2017, 631, 41-49.	0.8	45
333	Superradiance from Two Dimensional Brick-Wall Aggregates of Dye Molecules: The Role of Size and Shape for the Temperature Dependence. Physical Review Letters, 2017, 119, 097402.	2.9	30
334	Chemically specific termination control of oxide interfaces via layer-by-layer mean inner potential engineering. Nature Communications, 2018, 9, 2965.	5.8	34
335	Some geometrical aspects of diffracted waves formation on a reconstructed crystal face at RHEED. Surface Science, 2018, 677, 306-315.	0.8	3
336	Adsorbate induced manipulation of 1D atomic wires: Degradation of long-range order in the Si(553)-Au system. Surface Science, 2020, 700, 121673.	0.8	0
337	Thermally Induced Crossover from 2D to 1D Behavior in an Array of Atomic Wires: Silicon Dangling-Bond Solitons in Si(553)-Au. Physical Review Letters, 2020, 124, 016102.	2.9	14
338	Specific cation stoichiometry control of SrMnO <sub>3</sub> - $\delta$ thin films via RHEED oscillations. Applied Physics Letters, 2021, 118, .	1.5	2
339	In-situ quantification of the surface roughness for facile fabrications of atomically smooth thin films. Nano Research, 2022, 15, 1654-1659.	5.8	8
340	Surface and Thin Film Growth Studied by Reflection High Energy Electron Diffraction. NATO ASI Series Series B: Physics, 1989, , 267-282.	0.2	1
341	From Thermodynamics to Quantum Wires: A Review of Reflection High-Energy Electron Diffraction. NATO ASI Series Series B: Physics, 1990, , 225-243.	0.2	1
342	Intensity Oscillations in Reflection High Energy Electron Diffraction during Epitaxial Growth. , 1988, , 185-193.		1
343	Diffraction from Disordered Surfaces: An Overview. NATO ASI Series Series B: Physics, 1988, , 139-174.	0.2	40
344	Microprobe Reflection High-Energy Electron Diffraction. NATO ASI Series Series B: Physics, 1988, , 343-369.	0.2	4
345	RHEED Intensity Oscillations During MBE Growth of III-V Compounds - An Overview. NATO ASI Series Series B: Physics, 1988, , 397-417.	0.2	11
346	The Contribution of Atomic Steps to Reflection High Energy Electron Diffraction from Semiconductor Surfaces. NATO ASI Series Series B: Physics, 1988, , 427-447.	0.2	8

#	ARTICLE	IF	CITATIONS
347	Quantitative Studies of the Growth of Metals on GaAs(110) Using RHEED. NATO ASI Series Series B: Physics, 1988, , 475-488.	0.2	3
348	RHEED Intensity Oscillations in Metal Epitaxy. NATO ASI Series Series B: Physics, 1988, , 489-499.	0.2	4
349	Diffraction Studies of Epitaxy: Elastic, Inelastic and Dynamic Contributions to RHEED. NATO ASI Series Series B: Physics, 1987, , 69-94.	0.2	2
350	In-situ X-ray Diffraction at Synchrotrons and Free-Electron Laser Sources. Springer Series in Materials Science, 2014, , 39-58.	0.4	2
351	Reflection High Energy Electron Diffraction Studies of Diffusion and Cluster Formation During Molecular Beam Epitaxy. Springer Series in Surface Sciences, 1988, , 19-36.	0.3	3
352	Phases and Phase Diagrams of Xenon Adsorbed on Epitaxial NaCl(100) Films and on Ge(100). Springer Series in Surface Sciences, 1993, , 24-34.	0.3	2
353	RHEED and Photoemission Studies of Semiconductors Grown in-situ by MBE. Springer Series in Surface Sciences, 1985, , 196-219.	0.3	4
355	Atomic Geometry and Electronic Structure of Tetrahedrally Coordinated Compound Semiconductor Interfaces. Chemical Physics of Solid Surfaces, 1988, 5, 69-118.	0.3	4
356	Molecular Beam Epitaxy of III-V Compounds. Aspects of Growth Kinetics and Dynamics. Chemical Physics of Solid Surfaces, 1988, 5, 271-307.	0.3	3
357	Molecular Beam Epitaxy. The Materials Processingory and Practices, 1989, 7, 217-330.	0.1	5
358	Surfaces and Interfaces: Atomic-Scale Structure, Band Bending and Band Offsets. , 1992, , 281-417.		21
359	IN SITU OBSERVATION DURING MOLECULAR BEAM EPITAXY: IMPURITY INCORPORATION AND DISSIMILAR MATERIALS EPITAXIAL GROWTH ON GaAs(001). , 2001, , 351-386.		1
360	New Informations Obtained by Energy Filtered RHEED.. Hyomen Kagaku, 1996, 17, 447-453.	0.0	3
361	Growth of semiconductor layers studied by spot profile analysing low energy electron diffraction Part II<sup>1</sup>. Zeitschrift Fur Kristallographie - Crystalline Materials, 1999, 214, 684-721.	0.4	29
362	Engineering of Ferroic Orders in Thin Films by Anionic Substitution. Advanced Functional Materials, 2022, 32, 2107135.	7.8	9
363	Surface X-ray diffraction studies of crystal growth. , 2001, , 351-360.		1
364	Surface Step Information of Vicinal Si(001) in EF-RHEED Pattern.. Hyomen Kagaku, 2001, 22, 522-529.	0.0	2
365	Auger Electron Intensity Change by Wave Field of RHEED.. Hyomen Kagaku, 2002, 23, 497-502.	0.0	2

#	ARTICLE	IF	CITATIONS
366	In-Situ Investigation of the Growth of Low-Dimensional Structures. Studies in Computational Intelligence, 2009, , 557-572.	0.7	0
368	Domain Size Determination in Heteroepitaxial Systems from LEED Angular Profiles. Springer Series in Surface Sciences, 1985, , 366-374.	0.3	2
369	In Situ Study of MBE Growth Mechanisms Using RHEED Techniques " Some Consequences of Multiple Scattering. Springer Series in Solid-state Sciences, 1986, , 42-51.	0.3	3
370	Interpretation of intensity oscillation in RHEED during molecular beam epitaxial growth.. Nihon Kessho Gakkaishi, 1987, 29, 338-340.	0.0	0
371	Calculation of Rheed Intensity from Growing Surfaces. NATO ASI Series Series B: Physics, 1988, , 501-522.	0.2	0
373	LEED Investigations of Si MBE Onto Si(100). NATO ASI Series Series B: Physics, 1988, , 463-473.	0.2	0
374	Theory of Electron Scattering from Defect: Steps on Surfaces with Non-Equivalent Terraces. NATO ASI Series Series B: Physics, 1988, , 175-191.	0.2	0
375	Surface studies using microprobe reflection high-energy electron diffraction.. Nihon Kessho Gakkaishi, 1988, 30, 205-210.	0.0	0
376	Molecular Beam Epitaxy. , 1988, , 11-41.		0
377	THE INITIAL STAGES OF GROWTH OF SILICON ON Si(111) BY SLOW POSITRON ANNIHILATION LOW-ENERGY ELECTRON DIFFRACTION. , 1989, , 213-220.		0
378	In-Growth Characterization Techniques. Springer Series in Materials Science, 1989, , 120-158.	0.4	0
379	Rheed Oscillations During Growth of High-Tc Superconducting Oxides. , 1991, , 851-856.		0
380	Facet Coexistence in the Roughening Transition of Ag(110). Springer Proceedings in Physics, 1992, , 73-77.	0.1	1
381	Growth Kinetics in Two-Dimensional Phase Transitions. Chemical Physics of Solid Surfaces, 1994, , 215-257.	0.3	1
382	Characterization Techniques. Springer Series in Materials Science, 1996, , 135-227.	0.4	0
383	RHEED Intensity Oscillation during Epitaxial Growth.. Hyomen Kagaku, 1997, 18, 570-575.	0.0	1
384	Introduction to structural defects at surfaces. , 2018, , 151-167.		0
385	Fast Phase Retrieval from Reflection High Energy Electron Diffraction Intensities during Growth. E-Journal of Surface Science and Nanotechnology, 2018, 16, 97-100.	0.1	0

#	ARTICLE	IF	CITATIONS
389	Growth studies of heteroepitaxial oxide thin films using reflection high-energy electron diffraction. , 2022, , 3-36.		1
390	Kinetics of Convergence the Si(100) Surface Steps. Physics of the Solid State, 2022, 64, 609-615.	0.2	0